

*ABSTRACT AMENDMENT*

Replace the Abstract with:

A drive circuit includes a gate voltage detector that detects a gate-emitter voltage  $V_{ge}$  that appears between the gate and emitter of a power semiconductor device throughout a detection time period during which ~~a sampler allows the process of detecting~~ the gate-emitter voltage  $V_{ge}$  is sampled, and that recognizes the occurrence of an abnormality in the power semiconductor device when the gate-emitter voltage  $V_{ge}$  exceeds a reference value. Therefore, the drive circuit can protect the power semiconductor device with ~~higher~~ high reliability by promptly detecting the occurrence of a short circuit, even when the power semiconductor device is resistant to high voltages.